74HC257; 74HCT257

Quad 2-input multiplexer; 3-state

Rev. 05 — 13 January 2010   **Product data sheet**

1. General description

The 74HC257; 74HCT257 are high-speed Si-gate CMOS devices and are pin compatible with Low-power Schottky TTL (LSTTL).

The 74HC257 and 74HCT257 have four identical 2-input multiplexers with 3-state outputs, which select 4 bits of data from two sources and are controlled by a common data select input (S).

The data inputs from source 0 (1I0 to 4I0) are selected when input S is LOW and the data inputs from source 1 (1I1 to 4I1) are selected when S is HIGH. Data appears at the outputs (1Y to 4Y) in true (non-inverting) form from the selected inputs.

The 74HC257 and 74HCT257 are the logic implementation of a 4-pole, 2-position switch, where the position of the switch is determined by the logic levels applied to S. The outputs are forced to a high-impedance OFF-state when $\overline{OE}$ is HIGH.

The logic equations for the outputs are:

$$1\overline{Y} = \overline{OE} \bullet (1I1 \bullet S \bullet 1I0 \bullet \overline{S})$$

$$2\overline{Y} = \overline{OE} \bullet (2I1 \bullet S \bullet 2I0 \bullet \overline{S})$$

$$3\overline{Y} = \overline{OE} \bullet (3I1 \bullet S \bullet 3I0 \bullet \overline{S})$$

$$4\overline{Y} = \overline{OE} \bullet (4I1 \bullet S \bullet 4I0 \bullet \overline{S})$$

Except for their non-inverting (true) outputs the 74HC257; 74HCT257 are identical to the 74HC258.

2. Features

- Non-inverting data path
- 3-state outputs interface directly with system bus
- Complies with JEDEC standard no. 7A
- ESD protection:
    - HBM JESD22-A114E exceeds 2000 V
    - MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from −40 °C to +85 °C and from −40 °C to +125 °C

3. Ordering information

Table 1. Ordering information

| Type number	Package				
	Temperature range	Name	Description		Version
74HC257N	−40 °C to +125 °C	DIP16	plastic dual in-line package; 16 leads (300 mil)		SOT38-4
74HCT257N					
74HC257D	−40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm		SOT109-1
74HCT257D					
74HC257DB	−40 °C to +125 °C	SSOP16	plastic shrink small outline package; 16 leads; body width 5.3 mm		SOT338-1
74HCT257DB					
74HC257PW	−40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm		SOT403-1
74HCT257PW					

4. Functional diagram
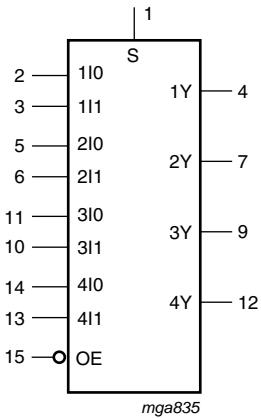

Fig 1. Logic symbol
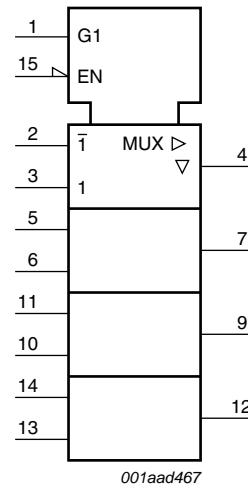
**Fig 2. IEC logic symbol**
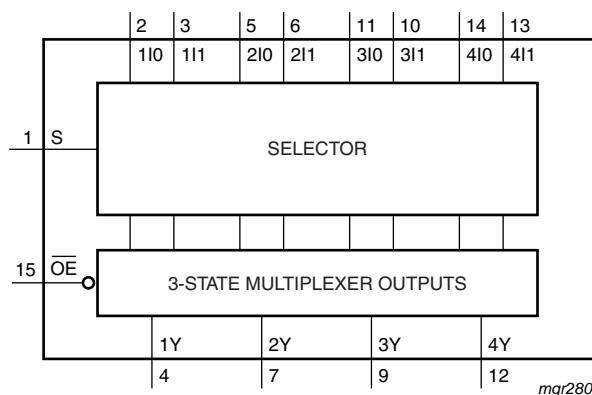
Fig 3.   Functional diagram
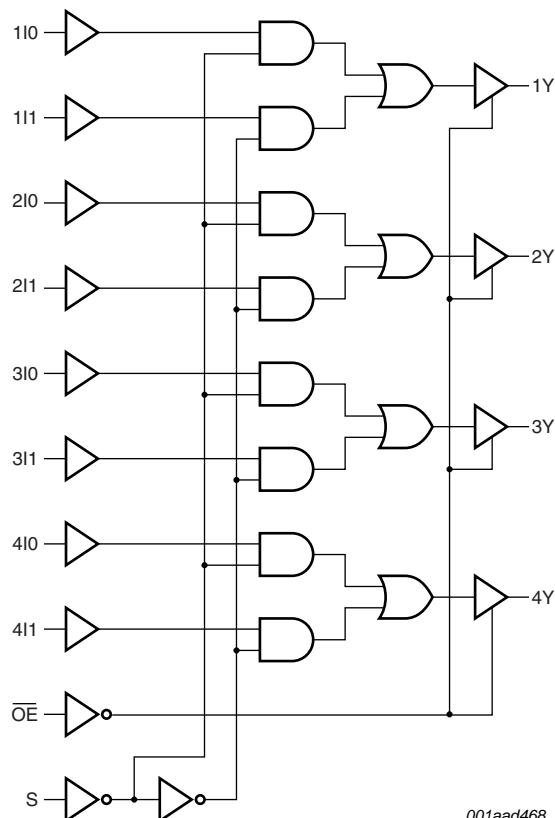
Fig 4.   Logic diagram

5. Pinning information

5.1 Pinning

74HC257
74HCT257

S	1		16	V_{CC}
1I0	2		15	$\overline{OE}$
1I1	3		14	4I0
1Y	4		13	4I1
2I0	5		12	4Y
2I1	6		11	3I0
2Y	7		10	3I1
GND	8		9	3Y

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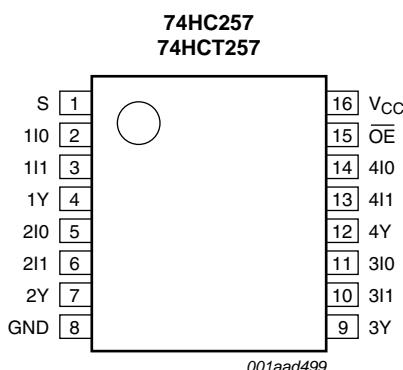
Fig 5. Pin configuration DIP16, SO16, SSOP16 and TSSOP16

5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
S	1	common data select input
1I0 to 4I0	2, 5, 11, 14	data input from source 0
1I1 to 4I1	3, 6, 10, 13	data input from source 1
1Y to 4Y	4, 7, 9, 12	3-state multiplexer output
GND	8	ground (0 V)
$\overline{OE}$	15	3-state output enable input (active LOW)
V_{CC}	16	supply voltage

6. Functional description

6.1 Function table

Table 3. Function table[1]

Control		Input		Output
$\overline{OE}$	S	nI0	nI1	nY
H	X	X	X	Z
L	H	X	L	L
L	H	X	H	H
L	L	L	X	L
L	L	H	X	H

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			−0.5	+7	V
I_{IK}	input clamping current	$V_I < -0.5$ V or $V_I > V_{CC} + 0.5$ V		-	±20	mA
I_{OK}	output clamping current	$V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V		-	±20	mA
I_O	output current	$V_O = -0.5$ V to $V_{CC} + 0.5$ V		-	±35	mA
I_{CC}	supply current			-	+70	mA
I_{GND}	ground current			-	−70	mA
T_{stg}	storage temperature			−65	+150	°C
P_{tot}	total power dissipation					
	DIP16 package		[1] -		750	mW
	SO16 package		[2] -		500	mW
	SSOP16 package		[3] -		500	mW
	TSSOP16 package		[3] -		500	mW

[1] For DIP16 packages: above 70 °C, P_{tot} derates linearly with 12 mW/K.

[2] For SO16 packages: above 70 °C, P_{tot} derates linearly with 8 mW/K.

[3] For SSOP16 and TSSOP16 packages: above 60 °C, P_{tot} derates linearly with 5.5 mW/K.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Type 74HC257						
V_{CC}	supply voltage		2.0	5.0	6.0	V
V_I	input voltage		0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	V
$\Delta t/\Delta V$	input transition rise and fall rates	$V_{CC} = 2.0$ V	-	-	625	ns
		$V_{CC} = 4.5$ V	-	1.67	139	ns
		$V_{CC} = 6.0$ V	-	-	83	ns
T_{amb}	ambient temperature		−40	-	+125	°C
Type 74HCT257						
V_{CC}	supply voltage		4.5	5.0	5.5	V
V_I	input voltage		0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	V
$\Delta t/\Delta V$	input transition rise and fall rates	$V_{CC} = 4.5$ V	-	1.67	139	ns
T_{amb}	ambient temperature		−40	-	+125	°C

9. Static characteristics

Table 6.   Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC257										
V_{IH}	HIGH-level input voltage	V_{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
		V_{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V_{CC} = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
		V_{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V_{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}								
		I_O = −20 μA; V_{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I_O = −20 μA; V_{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I_O = −20 μA; V_{CC} = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I_O = −6.0 mA; V_{CC} = 4.5 V	3.98	4.32	-	3.84	-	3.7	-	V
		I_O = −7.8 mA; V_{CC} = 6.0 V	5.48	5.81	-	5.34	-	5.2	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}								
		I_O = 20 μA; V_{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 20 μA; V_{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 20 μA; V_{CC} = 6.0 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 6.0 mA; V_{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
		I_O = 7.8 mA; V_{CC} = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
I_I	input leakage current	$V_I = V_{CC}$ or GND; V_{CC} = 6.0 V	-	-	±0.1	-	±1.0	±1.0	±1.0	μA
I_{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL}; $V_O = V_{CC}$ or GND; V_{CC} = 6.0 V	-	-	±0.5	-	±5.0	±10.0	±10.0	μA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; I_O = 0 A; V_{CC} = 6.0 V	-	-	8.0	-	80	160	160	μA
C_i	input capacitance		-	3.5	-					pF
74HCT257										
V_{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}; V_{CC} = 4.5 V								
		I_O = −20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I_O = −6 mA	3.98	4.32	-	3.84	-	3.7	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}; V_{CC} = 4.5 V				-	0.1	-	0.1	
		I_O = 20 μA	-	0	0.1	-	0.33	-	0.4	V
		I_O = 6.0 mA	-	0.15	0.26	-	±1.0	-	±1.0	V
I_I	input leakage current	$V_I = V_{CC}$ or GND; V_{CC} = 5.5 V	-	-	±0.1	-	±5.0	-	±10	μA

Table 6. **Static characteristics** *…continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
I_{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL}; V_{CC} = 5.5 V; $V_O = V_{CC}$ or GND per input pin; other inputs at V_{CC} or GND; I_O = 0 A	-	-	±0.5	-	80	-	160	µA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; I_O = 0 A; V_{CC} = 5.5 V	-	-	8.0					µA
ΔI_{CC}	additional supply current	$V_I = V_{CC} - 2.1$ V; other inputs at V_{CC} or GND; V_{CC} = 4.5 V to 5.5 V; I_O = 0 A								
		per input pin; nI0, nI1 inputs	-	40	144	-	180	-	196	µA
		per input pin; $\overline{OE}$ input	-	135	486	-	608	-	662	µA
		per input pin; S input	-	70	252	-	315	-	343	µA
C_I	input capacitance		-	3.5	-					pF

10. Dynamic characteristics

Table 7. **Dynamic characteristics**

Voltages are referenced to GND (ground = 0 V); For test circuit see Figure 8.

Symbol	Parameter	Conditions		25 °C		−40 °C to +85 °C	−40 °C to +125 °C	Unit
				Typ	Max	Max	Max	
74HC257								
t_{pd}	propagation delay	nI0 to nY or nI1 to nY; see Figure 6	[1]					
		V_{CC} = 2.0 V		36	110	140	165	ns
		V_{CC} = 4.5 V		13	22	28	33	ns
		V_{CC} = 5.0 V; C_L = 15 pF		11	-	-	-	ns
		V_{CC} = 6.0 V		10	19	24	28	ns
		S to nY; see Figure 6						
		V_{CC} = 2.0 V		47	150	190	225	ns
		V_{CC} = 4.5 V		17	30	38	45	ns
		V_{CC} = 5.0 V; C_L = 15 pF		14	-	-	-	ns
		V_{CC} = 6.0 V		14	26	33	38	ns
t_{en}	enable time	$\overline{OE}$ to nY; see Figure 7	[2]					
		V_{CC} = 2.0 V		33	150	190	225	ns
		V_{CC} = 4.5 V		12	30	38	45	ns
		V_{CC} = 6.0 V		10	26	33	38	ns
t_{dis}	disable time	$\overline{OE}$ to nY; see Figure 7	[3]					
		V_{CC} = 2.0 V		41	150	190	225	ns
		V_{CC} = 4.5 V		15	30	38	45	ns
		V_{CC} = 6.0 V		12	26	33	38	ns

Table 7. **Dynamic characteristics** *…continued*
*Voltages are referenced to GND (ground = 0 V); For test circuit see Figure 8.*

Symbol	Parameter	Conditions		25 °C		−40 °C to +85 °C	−40 °C to +125 °C	Unit
				Typ	Max	Max	Max	
t_t	transition time	see Figure 6	[4]					
		V_{CC} = 2.0 V		14	60	75	90	ns
		V_{CC} = 4.5 V		5	12	15	18	ns
		V_{CC} = 6.0 V		4	10	13	15	ns
C_{PD}	power dissipation capacitance	per multiplexer; V_I = GND to V_{CC}	[5]	45	-			pF
74HCT257								
t_{pd}	propagation delay	nI0 to nY or nI1 to nY; see Figure 6	[1]					
		V_{CC} = 4.5 V		16	30	38	45	ns
		V_{CC} = 5.0 V; C_L = 15 pF		13	-	-		ns
		S to nY; see Figure 6						
		V_{CC} = 4.5 V		20	35	44	53	ns
		V_{CC} = 5.0 V; C_L = 15 pF		17	-			ns
t_{en}	enable time	$\overline{OE}$ to nY; V_{CC} = 4.5 V; see Figure 7	[2]	15	30	38	45	ns
t_{dis}	disable time	$\overline{OE}$ to nY; V_{CC} = 4.5 V; see Figure 7	[3]	16	30	38	45	ns
t_t	transition time	V_{CC} = 4.5 V; see Figure 6	[4]	5	12	15	18	ns
C_{PD}	power dissipation capacitance	per multiplexer; V_I = GND to V_{CC}	[5]	45	-			pF

[1] t_{pd} is the same as t_{PHL}, t_{PLH}.

[2] t_{en} is the same as t_{PZH}, t_{PZL}.

[3] t_{dis} is the same as t_{PHZ}, t_{PLZ}.

[4] t_t is the same as t_{THL}, t_{TLH}.

[5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum(C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

$\sum(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

11. Waveforms
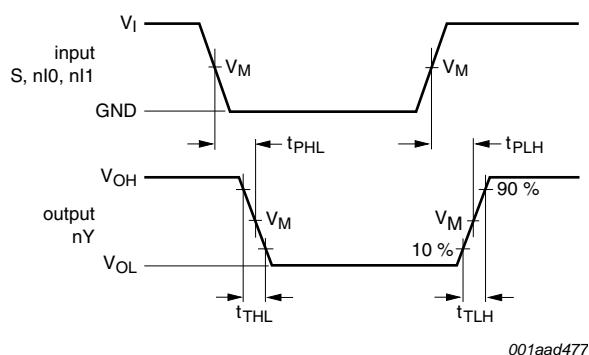
Measurement points are given in Table 8.

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 6. Propagation delays input (S, nI0, nI1) to output (nY) and output (nY) transition times
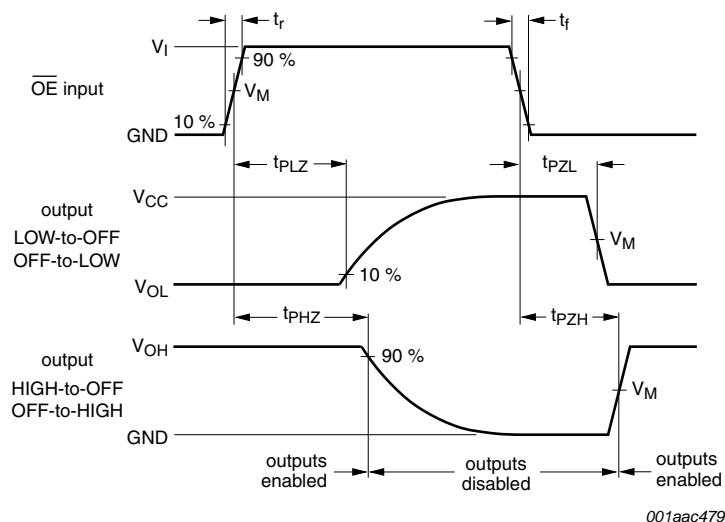

Measurement points are given in Table 8.

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 7. 3-state output enable and disable times

Table 8. Measurement points

Type	Input	Output
	V_M	V_M
74HC257	$0.5V_{CC}$	$0.5V_{CC}$
74HCT257	1.3 V	1.3 V
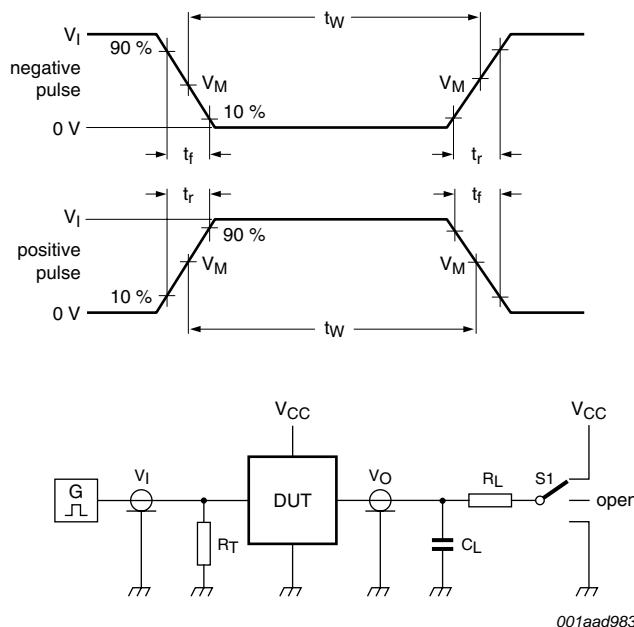
Measurement points are given in Table 8 and test data is given in Table 9.

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = Load capacitance including jig and probe capacitance.

R_L = Load resistor.

Fig 8.   **Test circuit for switching times**

Table 9.   **Test data**

Type	Input		Load		Switch position		
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
74HC257	V_{CC}	6 ns	50 pF	1 kΩ	open	GND	V_{CC}
74HCT257	3 V	6 ns	50 pF	1 kΩ	open	GND	V_{CC}

12. Package outline

DIP16: plastic dual in-line package; 16 leads (300 mil)　　　　　　　　　**SOT38-4**
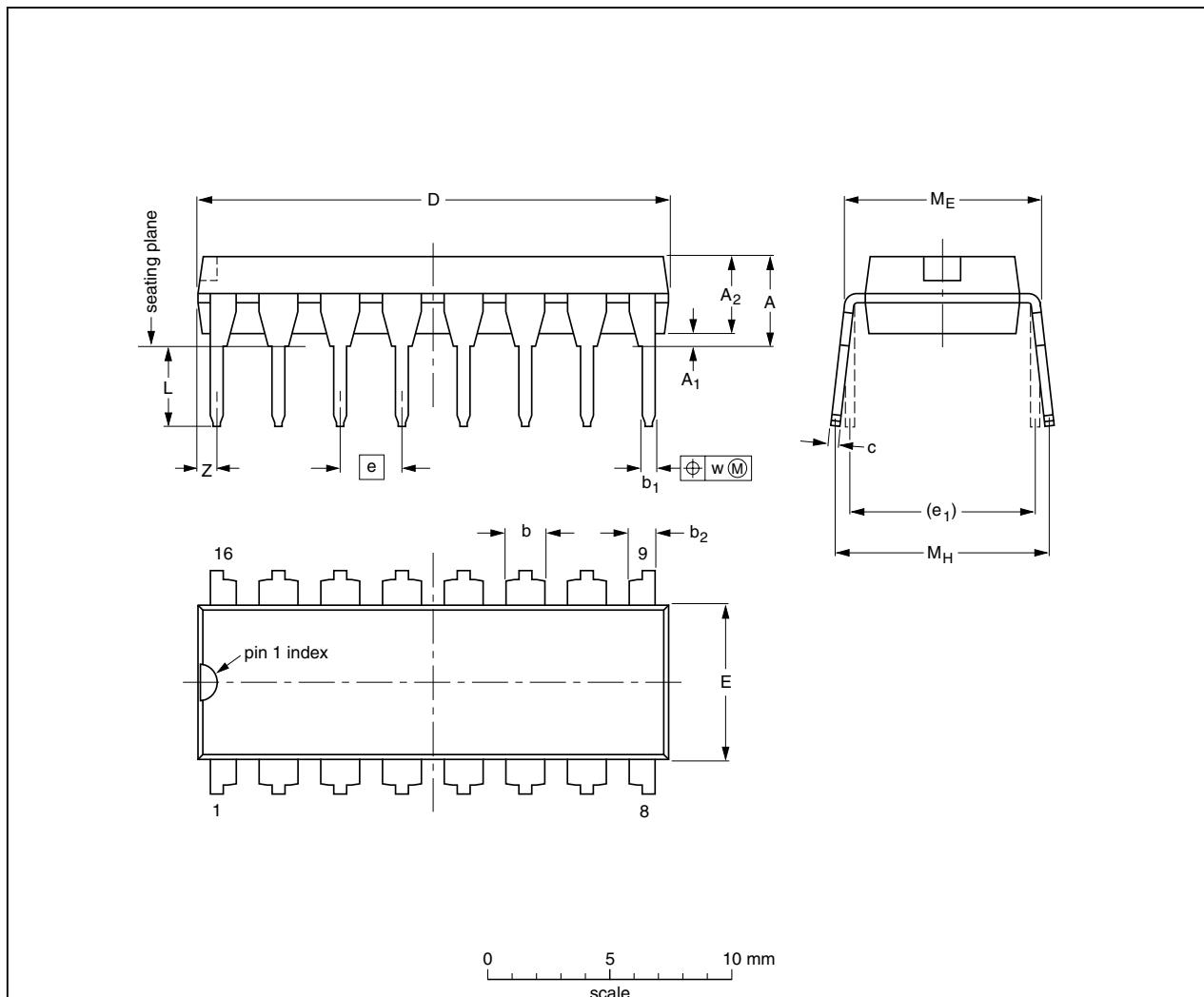
DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A₁ min.	A₂ max.	b	b₁	b₂	c	D(1)	E(1)	e	e₁	L	ME	MH	w	Z(1) max.
mm	4.2	0.51	3.2	1.73 1.30	0.53 0.38	1.25 0.85	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	0.76
inches	0.17	0.02	0.13	0.068 0.051	0.021 0.015	0.049 0.033	0.014 0.009	0.77 0.73	0.26 0.24	0.1	0.3	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.03

Note

1. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT38-4						95-01-14 03-02-13

Fig 9.　Package outline SOT38-4 (DIP16)

74HC_HCT257_5

SO16: plastic small outline package; 16 leads; body width 3.9 mm **SOT109-1**

DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	10.0 9.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8° 0°
inches	0.069	0.010 0.004	0.057 0.049	0.01	0.019 0.014	0.0100 0.0075	0.39 0.38	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.020	0.01	0.01	0.004	0.028 0.012	

Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT109-1	076E07	MS-012				99-12-27 03-02-19

Fig 10. Package outline SOT109-1 (SO16)

74HC_HCT257_5

SSOP16: plastic shrink small outline package; 16 leads; body width 5.3 mm

SOT338-1

pin 1 index

detail X

0   2.5   5 mm

scale
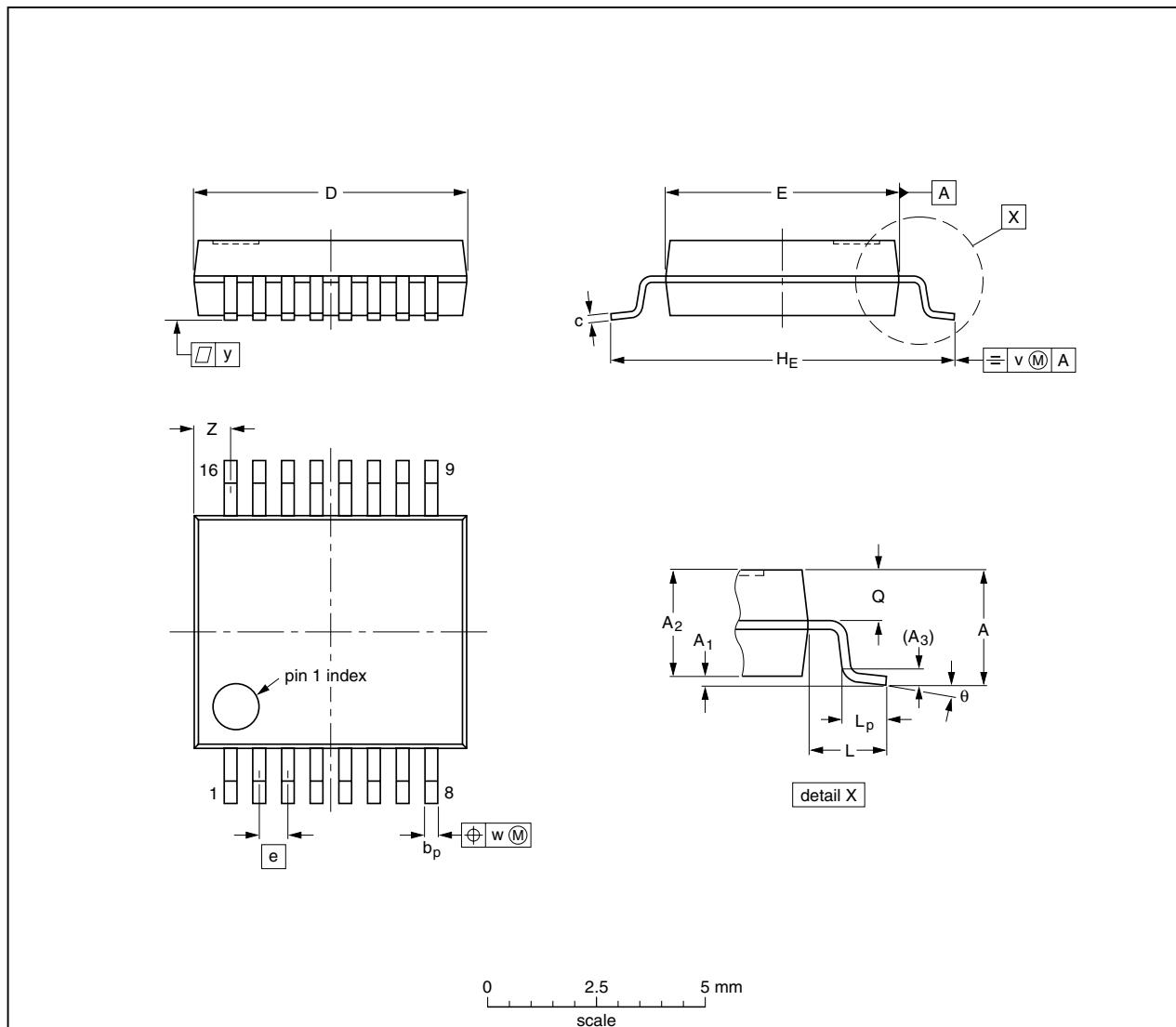
DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A₁	A₂	A₃	b_p	c	D [1]	E [1]	e	H_E	L	L_p	Q	v	w	y	Z [1]	θ
mm	2	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.00 0.55	8° 0°

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT338-1		MO-150				~~99-12-27~~ 03-02-19

Fig 11. Package outline SOT338-1 (SSOP16)

74HC_HCT257_5

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm SOT403-1

detail X

pin 1 index

0   2.5   5 mm
scale
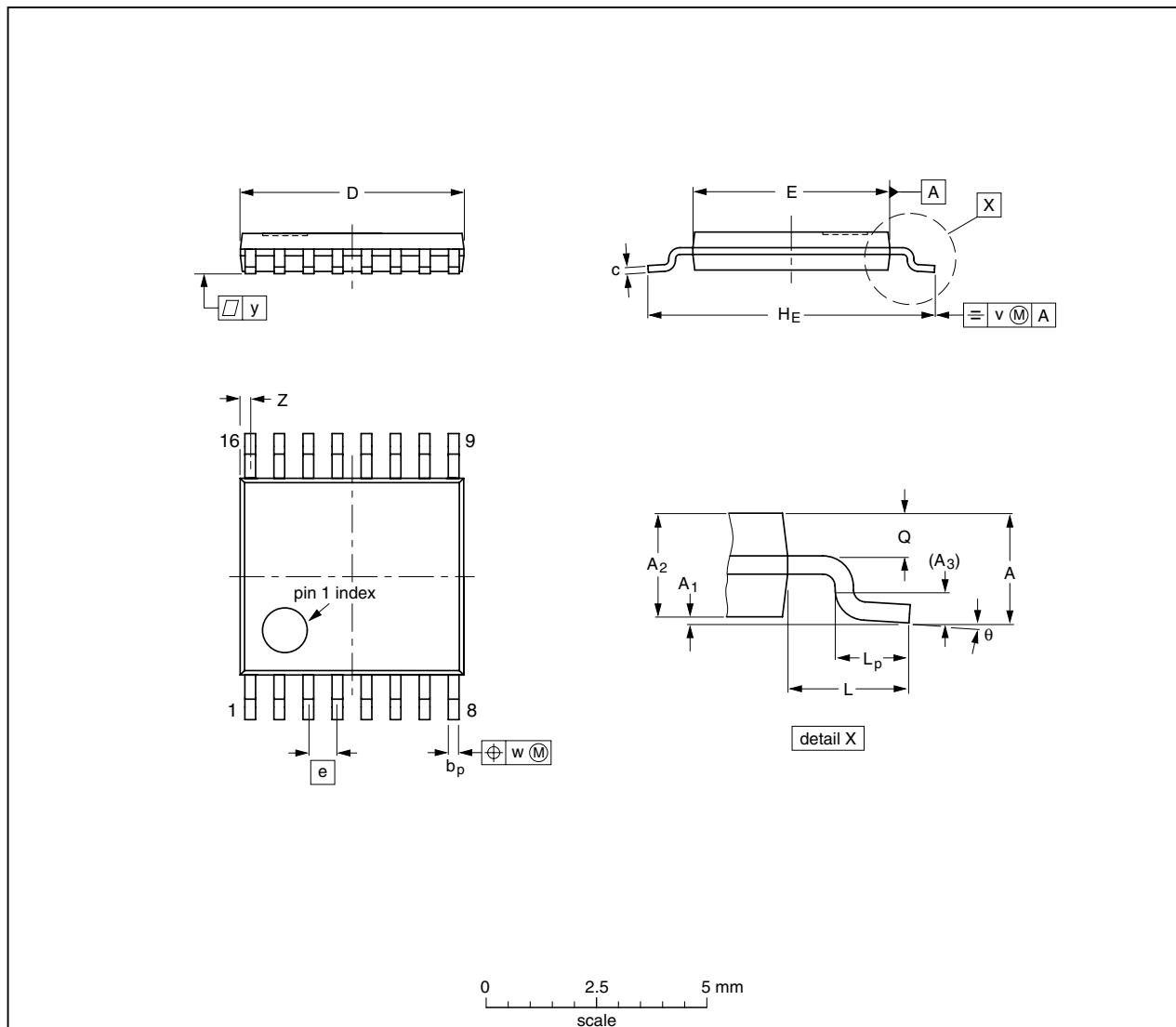
DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A₁	A₂	A₃	bₚ	c	D [1]	E [2]	e	H_E	L	Lₚ	Q	v	w	y	Z [1]	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.40 0.06	8° 0°

Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT403-1		MO-153				99-12-27 03-02-18

Fig 12. Package outline SOT403-1 (TSSOP16)

13. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT257_5	20100113	Product data sheet	-	74HC_HCT257_4
Modifications:	• Table 7 "Dynamic characteristics": changed $\overline{3OE}$ to $\overline{OE}$			
74HC_HCT257_4	20090608	Product data sheet	-	74HC_HCT257_3
74HC_HCT257_3	20050920	Product data sheet	-	74HC_HCT257_CNV_2
74HC_HCT257_CNV_2	19980930	Product specification	-	-

14. Legal information

14.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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16. Contents

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